Q1. A common base transistor amplifier has an input resistance of 20 Ω and output resistance of 100 k Ω . The collector load is 1 k Ω . If a signal of 500 mV is applied between emitter and base, find the voltage amplification. Assume α_{ac} to be nearly one.

Solution:

Fig.1 shows the conditions of the problem. Here the output resistance is very high as compared to input resistance, since the input junction (base to emitter) of the transistor is forward biased while the output junction (base to collector) is reverse biased.

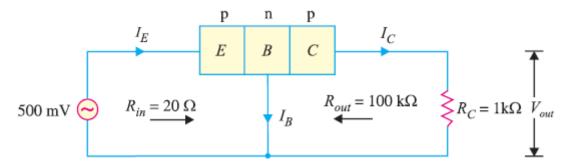


Fig. 1

Input current,
$$I_E = \frac{\text{Signal}}{R_{in}} = \frac{500 \text{ mV}}{20 \Omega} = 25 \text{ mA}$$
. Since α_{ac} is nearly 1, output current, $I_C = I_E = 25 \text{ mA}$.

Output voltage, $V_{out} = I_C R_C = 25 \text{ mA} \times 1 \text{ k}\Omega = 25 \text{ V}$
 \therefore Voltage amplification, $A_v = \frac{V_{out}}{\text{signal}} = \frac{25 \text{ V}}{500 \text{ mV}} = 50$

Q2. In a common base connection, $I_E = 1 \text{mA}$, $I_C = 0.95 \text{mA}$. Calculate the value of I_B .

Using the relation,
$$I_E = I_B + I_C$$

$$1 = I_B + 0.95$$

$$I_B = 1 - 0.95 = 0.05 \text{ mA}$$

Solution:

Q3. In a common base connection, current amplification factor is 0.9. If the emitter current is 1mA, determine the value of base current.

Now
$$\alpha = \frac{I_C}{I_E}$$
or
$$I_C = \alpha I_E = 0.9 \times 1 = 0.9 \text{ mA}$$
Also
$$I_E = I_B + I_C$$

$$\therefore \text{ Base current, } I_B = I_E - I_C = 1 - 0.9 = \textbf{0.1 mA}$$

Q4. In a common base connection, IC = 0.95 mA and IB = 0.05 mA. Find the value of α . Solution:

We know
$$I_E = I_B + I_C = 0.05 + 0.95 = 1 \text{ mA}$$

$$\therefore$$
 Current amplification factor, $\alpha = \frac{I_C}{I_E} = \frac{0.95}{1} = 0.95$

Q5. In a common base connection, the emitter current is 1mA. If the emitter circuit is open, the collector current is 50 μ A. Find the total collector current. Given that $\alpha = 0.92$.

Solution:

Here,
$$I_E = 1 \text{ mA}$$
, $\alpha = 0.92$, $I_{CBO} = 50 \text{ }\mu\text{A}$
 \therefore Total collector current, $I_C = \alpha I_E + I_{CBO} = 0.92 \times 1 + 50 \times 10^{-3}$
 $= 0.92 + 0.05 = 0.97 \text{ mA}$

Q6. In a common base connection, $\alpha=0.95$. The voltage drop across 2 k Ω resistance which is connected in the collector is 2V. Find the base current.

Solution:

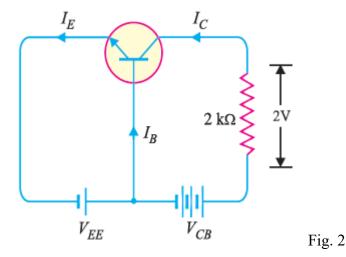


Fig. 2 shows the required common base connection.

The voltage drop across RC (= $2 \text{ k}\Omega$) is 2V.

:.
$$I_C = 2 \text{ V/2 k}\Omega = 1 \text{ mA}$$
 Now
$$\alpha = I_C/I_E$$

$$I_E = \frac{I_C}{\alpha} = \frac{1}{0.95} = 1.05 \text{ mA}$$
Using the relation, $I_E = I_B + I_C$

$$I_E = I_C - I_C = 1.05 - 1$$

$$I_B = I_E - I_C = 1.05 - 1$$
= 0.05 mA

Q7. For the common base circuit shown in Fig. 3, determine I_{C} and V_{CB} . Assume the transistor to be of silicon.

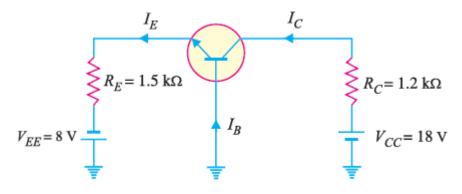


Fig. 3

Solution:

Since the transistor is of silicon, $V_{BE} = 0.7V$.

Applying Kirchhoff's voltage law to the emitter-side loop, we get,

$$V_{EE} = I_E R_E + V_{BE}$$
or
$$I_E = \frac{V_{EE} - V_{BE}}{R_E}$$

$$= \frac{8V - 0.7V}{1.5 \text{ k}\Omega} = 4.87 \text{ mA}$$

$$\therefore I_C \simeq I_E = 4.87 \text{ mA}$$

Applying Kirchhoff's voltage law to the collector-side loop, we have,

$$V_{CC} = I_C R_C + V_{CB}$$

 $\therefore V_{CB} = V_{CC} - I_C R_C$
 $= 18 \text{ V} - 4.87 \text{ mA} \times 1.2 \text{ k}\Omega = 12.16 \text{ V}$

Q8. Find the value of β if (i) $\alpha = 0.9$ (ii) $\alpha = 0.98$ (iii) $\alpha = 0.99$.

(i)
$$\alpha = 0.9$$

 $\beta = \frac{\alpha}{1 - \alpha} = \frac{0.9}{1 - 0.9} = 9$

(ii)
$$\alpha = 0.98$$

$$\beta = \frac{\alpha}{1-\alpha} = \frac{0.98}{1-0.98} = 49$$

(iii) $\alpha = 0.99$

$$\beta = \frac{\alpha}{1-\alpha} = \frac{0.99}{1-0.99} = 99$$

Q9. Calculate I_E in a transistor for which $\beta = 50$ and $I_B = 20 \mu A$.

Solution:

Now
$$\beta = \frac{I_C}{I_B}$$

$$\therefore I_C = \beta I_B = 50 \times 0.02 \text{ mA}$$
Using the relation, $I_E = I_B + I_C = 0.02 + 1 = 1.02 \text{ mA}$

Q10. Find the α rating of the transistor shown in Fig. 4. Hence determine the value of I_C using both α and β rating of the transistor.

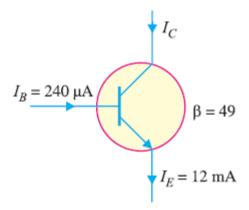


Fig. 4

Solution:

Fig. 8.20 shows the conditions of the problem.

$$\alpha = \frac{\beta}{1+\beta} = \frac{49}{1+49} = 0.98$$

The value of I_C can be found by using either α or β rating as under:

$$I_C = \alpha I_E = 0.98 (12 \text{ mA}) = 11.76 \text{ mA}$$

Also $I_C = \beta I_B = 49 (240 \text{ }\mu\text{A}) = 11.76 \text{ mA}$

Q11. For a transistor, $\beta=45$ and voltage drop across $1k\Omega$ which is connected in the collector circuit is 1 volt. Find the base current for common emitter connection.

Solution:

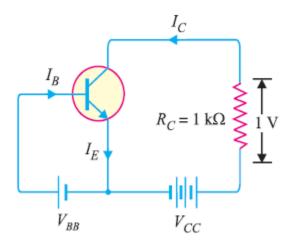


Fig. 5

Fig. 5 shows the required common emitter connection. The voltage drop across RC (= 1 k Ω) is 1 volt.

$$I_C = \frac{1V}{1 k \Omega} = 1 \text{ mA}$$
Now
$$\beta = \frac{I_C}{I_B}$$

$$I_B = \frac{I_C}{\beta} = \frac{1}{45} = 0.022 \text{ mA}$$

Q12. A transistor is connected in common emitter (CE) configuration in which collector supply is 8 V and the voltage drop across resistance $R_{\rm C}$ connected in the collector circuit is 0.5 V. The value of $R_{\rm C}$ = 800 Ω . If α = 0.96, determine : (i) collector-emitter voltage (ii) base current.

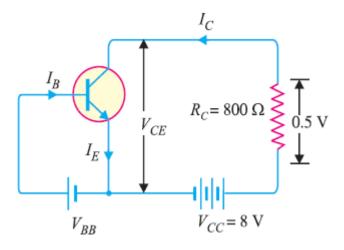


Fig.6

Fig. 6 shows the required common emitter connection with various values.

Collector-emitter voltage,

(i)
$$V_{CE} = V_{CC} - 0.5 = 8 - 0.5 = 7.5 \text{ V}$$

(ii)

The voltage drop across R_C (= 800 Ω) is 0.5 V.

$$C_C = \frac{0.5 \text{ V}}{800 \Omega} = \frac{5}{8} \text{ mA} = 0.625 \text{ mA}$$

$$\beta = \frac{\alpha}{1 - \alpha} = \frac{0.96}{1 - 0.96} = 24$$

:. Base current,
$$I_B = \frac{I_C}{\beta} = \frac{0.625}{24} = 0.026 \text{ mA}$$

Q13. An n-p-n transistor at room temperature has its emitter disconnected. A voltage of 5 V is applied between collector and base. With collector positive, a current of 0.2 μ A flows. When the base is disconnected and the same voltage is applied between collector and emitter, the current is found to be 20 μ A. Find α , I_E and I_B when collector current is 1 mA.

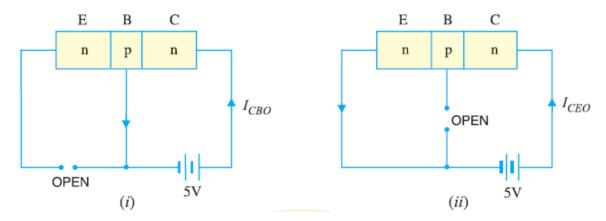


Fig. 7

When the emitter circuit is open as shown in Fig.7 (i), the collector-base junction is reverse biased. A small leakage current I_{CBO} flows due to minority carriers.

$$I_{CBO} = 0.2 \, \mu \text{A}$$
 given When base is open [See Fig. 8.23 (ii)], a small leakage current I_{CEO} flows due to minority carriers.
 $I_{CEO} = 20 \, \mu \text{A}$... given We know $I_{CEO} = \frac{I_{CBO}}{1 - \alpha}$ or $20 = \frac{0.2}{1 - \alpha}$... $\alpha = 0.99$ Now $I_{C} = \alpha I_{E} + I_{CBO}$ Here $I_{C} = 1 \, \text{mA} = 1000 \, \mu \text{A}$; $\alpha = 0.99$; $I_{CBO} = 0.2 \, \mu \text{A}$... $1000 = 0.99 \times I_{E} + 0.2$ or $I_{E} = \frac{1000 - 0.2}{0.99} = 1010 \, \mu \text{A}$ and $I_{B} = I_{E} - I_{C} = 1010 - 1000 = 10 \, \mu \text{A}$

Q14. The collector leakage current in a transistor is 300 μA in CE arrangement. If now the transistor is connected in CB arrangement, what will be the leakage current? Given that $\beta=120$.

$$I_{CEO} = 300 \,\mu\text{A}$$

Now,
$$I_{CEO} = \frac{I_{CBO}}{1 - \alpha}$$

$$I_{CEO} = \frac{I_{CBO}}{1 - \alpha}$$

$$I_{CEO} = (1 - \alpha)I_{CEO} = (1 - 0.992) \times 300 = 2.4 \,\mu\text{A}$$

Note that leakage current in CE arrangement (i.e. I_{CEO}) is much more than in CB arrangement (i.e. I_{CBO}).

Q15. For a certain transistor, $I_B = 20 \mu A$; $I_C = 2 mA$ and $\beta = 80$. Calculate I_{CBO} .

Solution:

or
$$I_{C} = \beta I_{B} + I_{CEO}$$

 $2 = 80 \times 0.02 + I_{CEO}$
 \therefore $I_{CEO} = 2 - 80 \times 0.02 = 0.4 \text{ mA}$
Now $\alpha = \frac{\beta}{\beta + 1} = \frac{80}{80 + 1} = 0.988$
 \therefore $I_{CBO} = (1 - \alpha) I_{CEO} = (1 - 0.988) \times 0.4 = 0.0048 \text{ mA}$

Q16. Using diagrams, explain the correctness of the relation $I_{CEO} = (\beta + 1)I_{CBO}$.

Solution:

The leakage current ICBO is the current that flows through the base-collector junction when emitter is open as shown is Fig. 8.

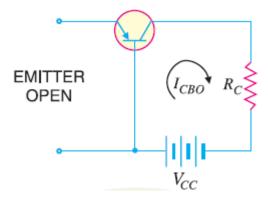


Fig. 8

When the transistor is in CE arrangement, the base current (i.e. I_{CBO}) is multiplied by β in the collector as shown in Fig. 9.

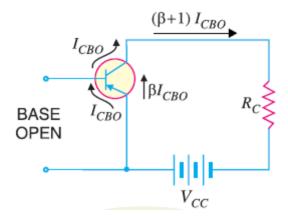


Fig.9

$$I_{CEO} = I_{CBO} + \beta I_{CBO} = (\beta + 1) I_{CBO}$$

Q17. Determine V_{CB} in the transistor circuit shown in Fig. 10 (i). The transistor is of silicon and has $\beta=150$.

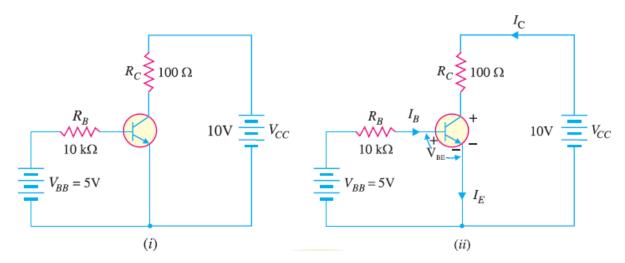


Fig.10

Fig. 10 (i) shows the transistor circuit while Fig. 10 (ii) shows the various currents and voltages along with polarities.

Applying Kirchhoff's voltage law to base-emitter loop, we have,

$$V_{BB} - I_B R_B - V_{BE} = 0$$
or
$$I_B = \frac{V_{BB} - V_{BE}}{R_B} = \frac{5V - 0.7V}{10 \, k\Omega} = 430 \, \mu\text{A}$$

$$\therefore I_C = \beta I_B = (150)(430 \, \mu\text{A}) = 64.5 \, \text{mA}$$
Now
$$V_{CE} = V_{CC} - I_C R_C$$

$$= 10V - (64.5 \, \text{mA}) \, (100\Omega) = 10V - 6.45V = 3.55V$$
We know that :
$$V_{CE} = V_{CB} + V_{BE}$$

$$\therefore V_{CB} = V_{CE} - V_{BE} = 3.55 - 0.7 = 2.85V$$

Q18. In a transistor, $I_B = 68 \mu A$, $I_E = 30 \text{ mA}$ and $\beta = 440$. Determine the α rating of the transistor. Then determine the value of I_C using both the α rating and β rating of the transistor.

Solution:

$$\alpha = \frac{\beta}{\beta + 1} = \frac{440}{440 + 1} = 0.9977$$

$$I_C = \alpha I_E = (0.9977) (30 \text{ mA}) = 29.93 \text{ mA}$$
Also
$$I_C = \beta I_B = (440) (68 \text{ } \mu\text{A}) = 29.93 \text{ mA}$$

Q19. A transistor has the following ratings : $I_{C\ (max)} = 500$ mA and $\beta_{max} = 300$. Determine the maximum allowable value of I_B for the device.

Solution:

$$I_{B (max)} = \frac{I_{C (max)}}{\beta_{max}} = \frac{500 \text{ mA}}{300} = 1.67 \text{ mA}$$

For this transistor, if the base current is allowed to exceed 1.67 mA, the collector current will exceed its maximum rating of 500 mA and the transistor will probably be destroyed.

Q20. Fig. 11 shows the open circuit failures in a transistor. What will be the circuit behaviour in each case?

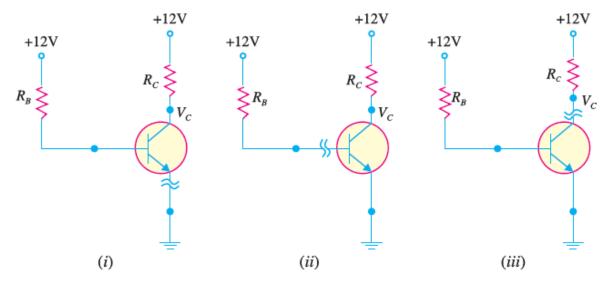


Fig. 11

Fig 11 shows the open circuit failures in a transistor. We shall discuss the circuit behaviour in each case.

(i) Open emitter:

Fig. 11 (i) shows an open emitter failure in a transistor. Since the collector diode is not forward biased, it is OFF and there can be neither collector current nor base current. Therefore, there will be no voltage drops across either resistor and the voltage at the base and at the collector leads of the transistor will be 12V.

(ii) Open-base:

Fig. 11 (ii) shows an open base failure in a transistor. Since the base is open, there can be no base current so that the transistor is in cut-off. Therefore, all the transistor currents are 0A. In this case, the base and collector voltages will both be at 12V.

(iii) Open collector:

Fig. 11 (iii) shows an open collector failure in a transistor. In this case, the emitter diode is still ON, so we expect to see 0.7V at the base. However, we will see 12V at the collector because there is no collector current.

Q21. For the circuit shown in Fig. 12, draw the d.c. load line.

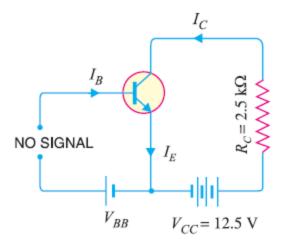


Fig.12

Solution:

The collector-emitter voltage V_{CE} is given by ;

$$V_{CE} = V_{CC} - I_C R_C$$
 When $I_C = 0$, then,
$$V_{CE} = V_{CC} = 12.5 \text{ V}$$

This locates the point B of the load line on the collector-emitter voltage axis.

When
$$V_{CE} = 0$$
, then,
 $I_C = V_{CC}/R_C = 12.5 \text{ V}/2.5 \text{ k}\Omega = 5 \text{ mA}$

This locates the point A of the load line on the collector current axis. By joining these two points, we get the d.c. load line AB as shown in Fig. 13.

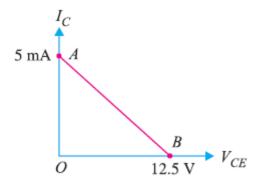


Fig.13

Q22. In the circuit diagram shown in Fig. 14, if V_{CC} = 12V and R_C = 6 k Ω , draw the d.c. load line. What will be the Q point if zero signal base current is 20 μ A and β = 50 ?

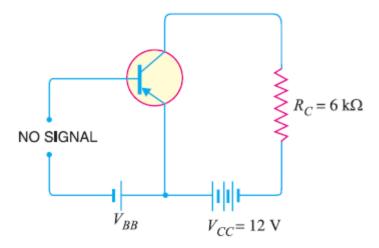


Fig.14

Solution:

The collector-emitter voltage V_{CE} is given by :

$$V_{CE} = V_{CC} - I_C R_C$$

When $I_C = 0$, $V_{CE} = V_{CC} = 12$ V. This locates the point B of the load line.

When
$$V_{CE} = 0$$
, $I_C = V_{CC} / R_C = 12 \text{ V/6 k}\Omega = 2 \text{ mA}$.

This locates the point A of the load line. By joining these two points, load line AB is constructed as shown in 15.

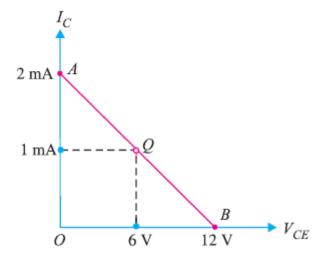


Fig. 15

Zero signal base current, $I_B = 20 \,\mu\text{A} = 0.02 \,\text{mA}$

Current amplification factor, $\beta = 50$

 \therefore Zero signal collector current, $I_C = \beta I_B = 50 \times 0.02 = 1 \text{ mA}$

Zero signal collector-emitter voltage is

$$V_{CE} = V_{CC} - I_C R_C = 12 - 1 \text{ mA} \times 6 \text{ k } \Omega = 6 \text{ V}$$

∴ Operating point is 6 V, 1 mA.

Fig. 15 shows the Q point. Its co-ordinates are $I_C = 1$ mA and $V_{CE} = 6$ V.

Q23. In a transistor circuit, collector load is 4 k Ω whereas quiescent current (zero signal collector current) is 1 mA. (i) What is the operating point if V_{CC} = 10 V? (ii) What will be the operating point if R_C = 5 k Ω ?

Solution:
$$V_{CC} = 10 \text{ V}, I_C = 1 \text{ mA}$$

- (i) When collector load $R_C = 4 \text{ k }\Omega$, then,
- $V_{CE} = V_{CC} I_C R_C = 10 1 \text{ mA} \times 4 \text{ k } \Omega = 10 4 = 6 \text{ V}$ \therefore Operating point is 6 V, 1 mA.
- (ii) When collector load $R_C = 5 \text{ k }\Omega$, then,

$$V_{CE}^{-} = V_{CC} - I_C R_C = 10 - 1 \text{ mA} \times 5 \text{ k} \Omega = 10 - 5 = 5 V$$

.. Operating point is 5 V, 1 mA.

Q24. Determine the Q point of the transistor circuit shown in Fig. 16. Also draw the d.c. load line. Given $\beta = 200$ and $V_{BE} = 0.7V$.

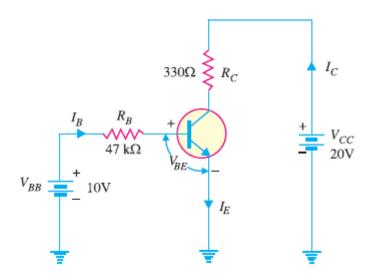


Fig. 16

The presence of resistor R_B in the base circuit should not disturb you because we can apply Kirchhoff's voltage law to find the value of I_B and hence I_C (= βI_B). Referring to Fig. 16 and applying Kirchhoff's voltage law to base-emitter loop, we have,

$$V_{BB} - I_B R_B - V_{BE} = 0$$

$$I_B = \frac{V_{BB} - V_{BE}}{R_B} = \frac{10V - 0.7V}{47 \, k\Omega} = 198 \, \mu\text{A}$$
Now
$$I_C = \beta I_B = (200)(198 \, \mu\text{A}) = 39.6 \, \text{mA}$$
Also
$$V_{CE} = V_{CC} - I_C R_C = 20V - (39.6 \, \text{mA}) \, (330 \, \Omega) = 20V - 13.07V = 6.93V$$
Therefore, the Q-point is $I_C = 39.6 \, \text{mA}$ and $V_{CE} = 6.93V$.

D.C. load line:

In order to draw the d.c. load line, we need two end points.

$$V_{CE} = V_{CC} - I_C R_C$$

When $I_C = 0$, $V_{CE} = V_{CC} = 20V$. This locates the point B of the load line on the collector-emitter voltage axis as shown in Fig. 17.

When $V_{CE} = 0$, $I_C = V_{CC} / R_C = 20V/330\Omega = 60.6$ mA. This locates the point A of the load line on the collector current axis.

By joining these two points, d.c. load line AB is constructed as shown in Fig. 17.

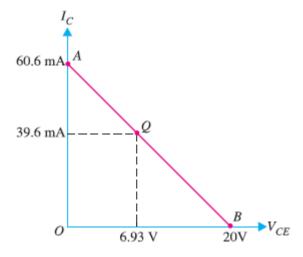


Fig. 17

Q25. Determine the Q point of the transistor circuit shown in Fig. 18. Also draw the d.c. load line. Given $\beta = 100$ and $V_{BE} = 0.7V$.

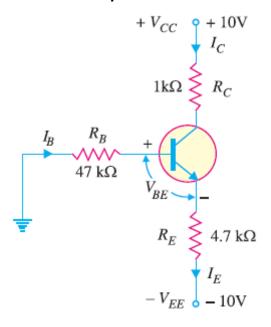


Fig.18

Solution:

The transistor circuit shown in Fig. 18 may look complex but we can easily apply Kirchhoff's voltage law to find the various voltages and currents in the circuit.

Applying Kirchhoff's voltage law to the base-emitter loop, we have,

$$-I_B R_B - V_{BE} - I_E R_E + V_{EE} = 0$$
 or $V_{EE} = I_B R_B + I_E R_E + V_{BE}$

Now $I_C = \beta I_B$ and $I_C \simeq I_E$. $\therefore I_B = I_E/\beta$. Putting $I_B = I_E/\beta$ in the above equation, we have,

$$V_{EE} = \left(\frac{I_E}{\beta}\right) R_B + I_E R_E + V_{BE}$$
 or
$$I_E \left(\frac{R_B}{\beta} + R_E\right) = V_{EE} - V_{BE} \text{ or } I_E = \frac{V_{EE} - V_{BE}}{R_E + R_B / \beta}$$
 Since $I_C \simeq I_E$,
$$I_C = \frac{V_{EE} - V_{BE}}{R_E + R_B / \beta} = \frac{10 \text{V} - 0.7 \text{V}}{4.7 \text{ k}\Omega + 47 \text{ k}\Omega / 100} = \frac{9.3 \text{ V}}{5.17 \text{ k}\Omega} = 1.8 \text{ mA}$$

Applying Kirchhoff's voltage law to the collector side, we have,

$$\begin{split} V_{CC} - I_C \, R_C - V_{CE} - I_E \, R_E + V_{EE} &= 0 \\ \text{or} \qquad V_{CE} &= V_{CC} + V_{EE} - I_C \, (R_C + R_E) \\ &= 10 \text{V} + 10 \text{V} - 1.8 \text{ mA} \, (1 \, \text{k}\Omega + 4.7 \, \text{k}\Omega) = 9.74 \text{V} \end{split}$$

Therefore, the operating point of the circuit is $I_C = 1.8 \text{ mA}$ and $V_{CE} = 9.74 \text{V}$.

D.C. load line:

The d.c. load line can be constructed as under:

$$V_{CE} = V_{CC} + V_{EE} - I_C (R_C + R_E)$$

When $I_C = 0$; $V_{CE} = V_{CC} + V_{EE} = 10\text{V} + 10\text{V} = 20\text{V}$. This locates the first point B (OB = 20V) of the load line on the collector-emitter voltage axis. When $V_{CE} = 0$, $I_C = \frac{V_{CC} + V_{EE}}{R_C + R_E} = \frac{10V + 10V}{1 k\Omega + 4.7 k\Omega} = \frac{20V}{5.7 k\Omega} = 3.51 \text{ mA}$

$$I_C = \frac{V_{CC} + V_{EE}}{R_C + R_E} = \frac{10V + 10V}{1 k\Omega + 4.7 k\Omega} = \frac{20V}{5.7 k\Omega} = 3.51 \text{ mA}$$

This locates the second point A (OA = 3.51 mA) of the load line on the collector current axis. By joining points A and B, d.c. load line AB is constructed as shown in Fig. 19.

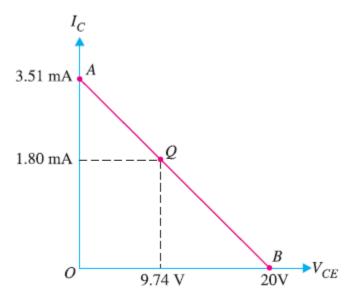


Fig.19